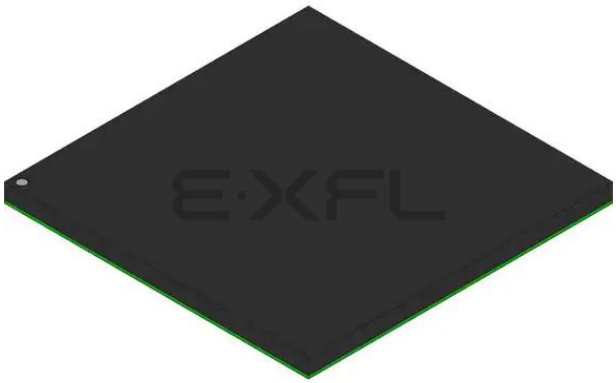

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	2432
Number of Logic Elements/Cells	24320
Total RAM Bits	311296
Number of I/O	508
Number of Gates	1537000
Voltage - Supply	1.71V ~ 1.89V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	672-BGA
Supplier Device Package	672-FBGA (27x27)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=ep20k600cf672c8

…and More Features

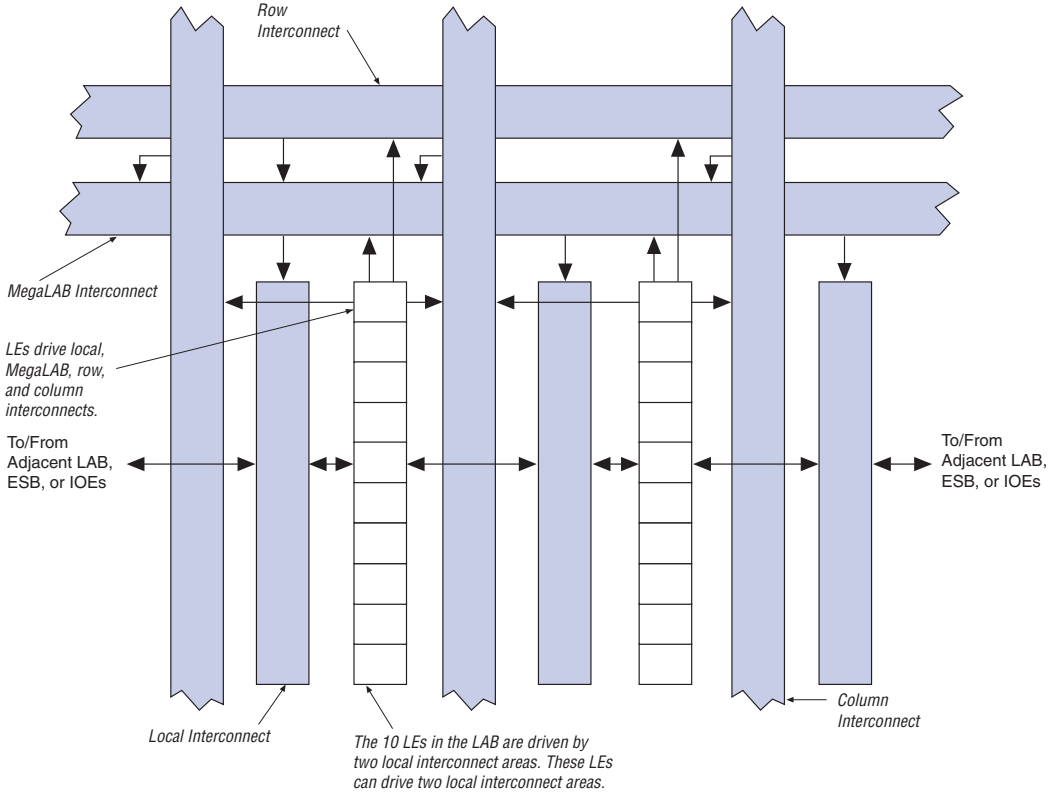
- Low-power operation design
  - 1.8-V supply voltage (see Table 2)
  - Copper interconnect reduces power consumption
  - MultiVolt™ I/O support for 1.8-V, 2.5-V, and 3.3-V interfaces
  - ESBs offering programmable power-saving mode
- Flexible clock management circuitry with up to four phase-locked loops (PLLs)
  - Built-in low-skew clock tree
  - Up to eight global clock signals
  - ClockLock™ feature reducing clock delay and skew
  - ClockBoost™ feature providing clock multiplication and division
  - ClockShift™ feature providing programmable clock phase and delay shifting
- Powerful I/O features
  - Compliant with peripheral component interconnect Special Interest Group (PCI SIG) ***PCI Local Bus Specification, Revision 2.2*** for 3.3-V operation at 33 or 66 MHz and 32 or 64 bits
  - Support for high-speed external memories, including DDR synchronous dynamic RAM (SDRAM) and ZBT static RAM (SRAM)
  - 16 input and 16 output LVDS channels at 840 megabits per second (Mbps)
  - Direct connection from I/O pins to local interconnect providing fast t_{CO} and t_{SU} times for complex logic
  - MultiVolt I/O support for 1.8-V, 2.5-V, and 3.3-V interfaces
  - Programmable clamp to V_{CCIO}
  - Individual tri-state output enable control for each pin
  - Programmable output slew-rate control to reduce switching noise
  - Support for advanced I/O standards, including low-voltage differential signaling (LVDS), LVPECL, PCI-X, AGP, CTT, SSTL-3 and SSTL-2, GTL+, and HSTL Class I
  - Supports hot-socketing operation
  - Pull-up on I/O pins before and during configuration

Table 2. APEX 20KC Supply Voltages

Feature	Voltage
Internal supply voltage (V_{CCINT})	1.8 V
MultiVolt I/O interface voltage levels (V_{CCIO})	1.8 V, 2.5 V, 3.3 V, 5.0 V *(1)*

Note to Table 2:
(1) APEX 20KC devices can be 5.0-V tolerant by using an external resistor.

Figure 3. LAB Structure

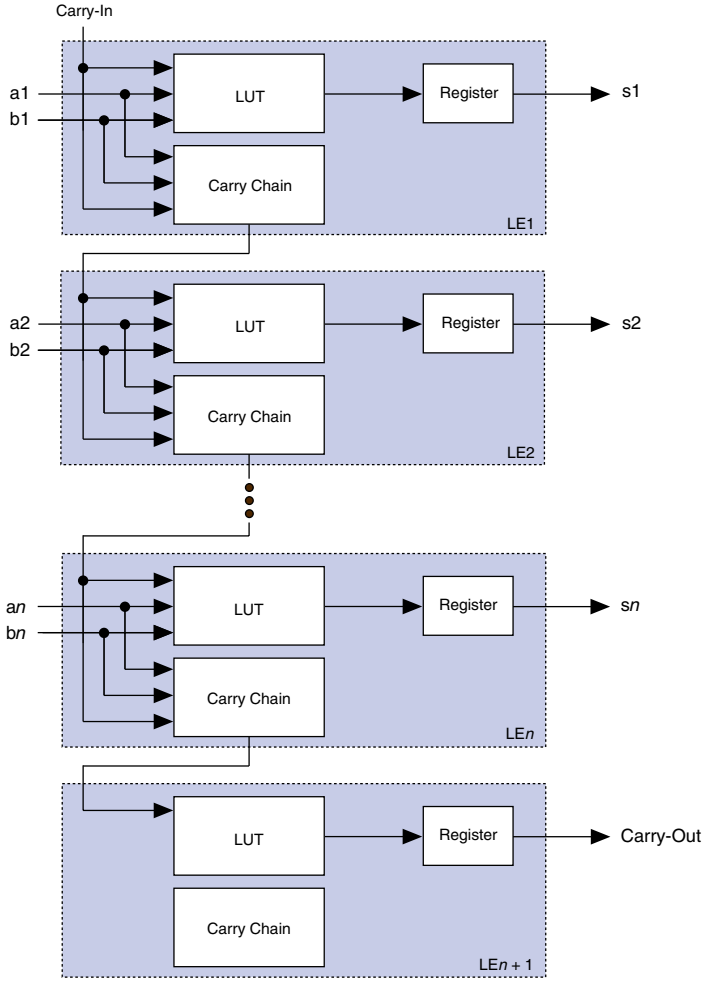


Each LAB contains dedicated logic for driving control signals to its LEs and ESBs. The control signals include clock, clock enable, asynchronous clear, asynchronous preset, asynchronous load, synchronous clear, and synchronous load signals. A maximum of six control signals can be used at a time. Although synchronous load and clear signals are generally used when implementing counters, they can also be used with other functions.

Each LAB can use two clocks and two clock enable signals. Each LAB's clock and clock enable signals are linked (e.g., any LE in a particular LAB using `CLK1` will also use `CLKENA1`). LEs with the same clock but different clock enable signals either use both clock signals in one LAB or are placed into separate LABs.

If both the rising and falling edges of a clock are used in a LAB, both LAB-wide clock signals are used.

Figure 6. APEX 20KC Carry Chain



The counter mode uses two 3-input LUTs: one generates the counter data, and the other generates the fast carry bit. A 2-to-1 multiplexer provides synchronous loading, and another AND gate provides synchronous clearing. If the cascade function is used by an LE in counter mode, the synchronous clear or load overrides any signal carried on the cascade chain. The synchronous clear overrides the synchronous load. LEs in arithmetic mode can drive out registered and unregistered versions of the LUT output.

Clear & Preset Logic Control

Logic for the register's clear and preset signals is controlled by LAB-wide signals. The LE directly supports an asynchronous clear function. The Quartus II Compiler can use a NOT-gate push-back technique to emulate an asynchronous preset or to emulate simultaneous preset and clear or asynchronous load. However, this technique uses three additional LEs per register. All emulation is performed automatically when the design is compiled. Registers that emulate simultaneous preset and load will enter an unknown state upon power-up or when the chip-wide reset is asserted.

In addition to the two clear and preset modes, APEX 20KC devices provide a chip-wide reset pin (DEV_CLRn) that resets all registers in the device. Use of this pin is controlled through an option in the Quartus II software that is set before compilation. The chip-wide reset overrides all other control signals. Registers using an asynchronous preset are preset when the chip-wide reset is asserted; this effect results from the inversion technique used to implement the asynchronous preset.

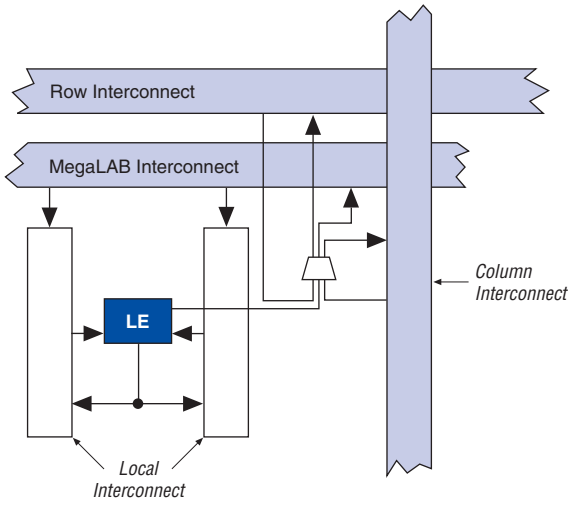
FastTrack Interconnect

In the APEX 20KC architecture, connections between LEs, ESBs, and I/O pins are provided by the FastTrack interconnect. The FastTrack interconnect is a series of continuous horizontal and vertical routing channels that traverse the device. This global routing structure provides predictable performance, even in complex designs. In contrast, the segmented routing in FPGAs requires switch matrices to connect a variable number of routing paths, increasing the delays between logic resources and reducing performance.

The FastTrack interconnect consists of row and column interconnect channels that span the entire device. The row interconnect routes signals throughout a row of MegaLAB structures; the column interconnect routes signals throughout a column of MegaLAB structures. When using the row and column interconnect, an LE, IOE, or ESB can drive any other LE, IOE, or ESB in a device. See Figure 9.

Figure 11 shows the intersection of a row and column interconnect, and how these forms of interconnects and LEs drive each other.

Figure 11. Driving the FastTrack Interconnect



APEX 20KC devices include an enhanced interconnect structure for faster routing of input signals with high fan-out. Column I/O pins can drive the FastRow™ interconnect, which routes signals directly into the local interconnect without having to drive through the MegaLAB interconnect. The FastRow lines traverse two MegaLAB structures. Also, these pins can drive the local interconnect directly for fast setup times. On EP20K400C and larger devices, the FastRow interconnect drives the two MegaLAB structures in the top left corner, the two MegaLAB structures in the two right corner, the two MegaLAB structures in the bottom left corner, and the two MegaLAB structures in the bottom right corner. On EP20K200C and smaller devices, FastRow interconnect drives the two MegaLAB structures on the top and the two MegaLAB structures on the bottom of the device. On all devices, the FastRow interconnect drives all local interconnect in the appropriate MegaLAB structures except the end local interconnect on the side of the MegaLAB opposite the ESB. Pins using the FastRow interconnect achieve a faster set-up time, as the signal does not need to use a MegaLAB interconnect line to reach the destination LE. Figure 12 shows the FastRow interconnect.

ESBs can implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (WE) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the WE signal. In contrast, the ESB's synchronous RAM generates its own WE signal and is self-timed with respect to the global clock. Circuits using the ESB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

ESB inputs are driven by the adjacent local interconnect, which in turn can be driven by the FastTrack or MegaLAB interconnect. Because the ESB can be driven by the local interconnect, an adjacent LE can drive it directly for fast memory access. ESB outputs drive the FastTrack and MegaLAB interconnects. In addition, ten ESB outputs, nine of which are unique output lines, drive the local interconnect for fast connection to adjacent LEs or for fast feedback product-term logic.

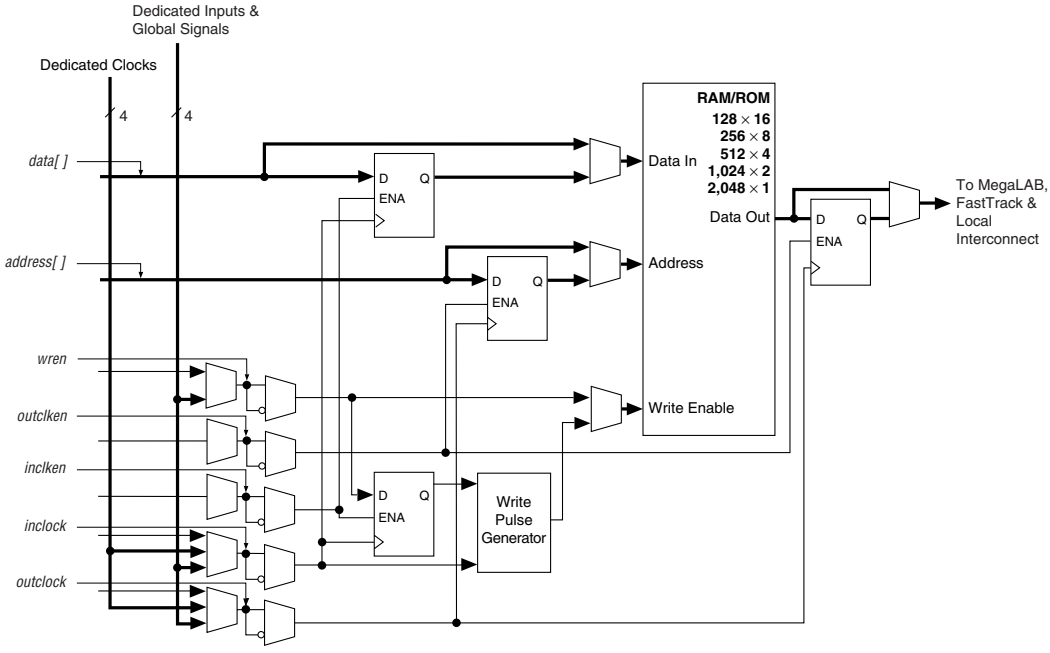
When implementing memory, each ESB can be configured in any of the following sizes: 128 × 16, 256 × 8, 512 × 4, 1,024 × 2, or 2,048 × 1. By combining multiple ESBs, the Quartus II software implements larger memory blocks automatically. For example, two 128 × 16 RAM blocks can be combined to form a 128 × 32 RAM block, and two 512 × 4 RAM blocks can be combined to form a 512 × 8 RAM block. Memory performance does not degrade for memory blocks up to 2,048 words deep. Each ESB can implement a 2,048-word-deep memory; the ESBs are used in parallel, eliminating the need for any external control logic and its associated delays.

To create a high-speed memory block that is more than 2,048 words deep, ESBs drive tri-state lines. Each tri-state line connects all ESBs in a column of MegaLAB structures, and drives the MegaLAB interconnect and row and column FastTrack interconnect throughout the column. Each ESB incorporates a programmable decoder to activate the tri-state driver appropriately. For instance, to implement 8,192-word-deep memory, four ESBs are used. Eleven address lines drive the ESB memory, and two more drive the tri-state decoder. Depending on which 2,048-word memory page is selected, the appropriate ESB driver is turned on, driving the output to the tri-state line. The Quartus II software automatically combines ESBs with tri-state lines to form deeper memory blocks. The internal tri-state control logic is designed to avoid internal contention and floating lines. See Figure 18.

Single-Port Mode

The APEX 20KC ESB also supports a single-port mode, which is used when simultaneous reads and writes are not required. See Figure 22.

Figure 22. ESB in Single-Port Mode *Note (1)*



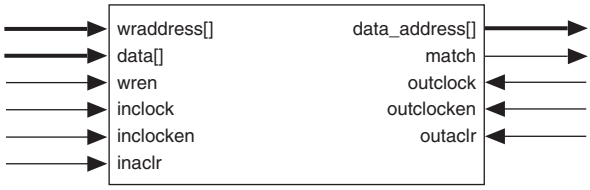
Note to Figure 22:

(1) All registers can be asynchronously cleared by ESB local interconnect signals, global signals, or the chip-wide reset.

Content-Addressable Memory

In APEX 20KC devices, the ESB can implement CAM. CAM can be thought of as the inverse of RAM. When read, RAM outputs the data for a given address. Conversely, CAM outputs an address for a given data word. For example, if the data `FA12` is stored in address `14`, the CAM outputs `14` when `FA12` is driven into it.

Figure 23. APEX 20KC CAM Block Diagram



CAM can be used in any application requiring high-speed searches, such as networking, communications, data compression, and cache management.

The APEX 20KC on-chip CAM provides faster system performance than traditional discrete CAM. Integrating CAM and logic into the APEX 20KC device eliminates off-chip and on-chip delays, improving system performance.

When in CAM mode, the ESB implements 32-word, 32-bit CAM. Wider or deeper CAM can be implemented by combining multiple CAMs with some ancillary logic implemented in LEs. The Quartus II software combines ESBs and LEs automatically to create larger CAMs.

CAM supports writing "don't care" bits into words of the memory. The "don't care" bit can be used as a mask for CAM comparisons; any bit set to "don't care" has no effect on matches.

The output of the CAM can be encoded or unencoded. When encoded, the ESB outputs an encoded address of the data's location. For instance, if the data is located in address `12`, the ESB output is `12`. When unencoded, the ESB uses its 16 outputs to show the location of the data over two clock cycles. In this case, if the data is located in address `12`, the 12th output line goes high. When using unencoded outputs, two clock cycles are required to read the output because a 16-bit output bus is used to show the status of 32 words.

The encoded output is better suited for designs that ensure duplicate data is not written into the CAM. If duplicate data is written into two locations, the CAM's output will be incorrect. If the CAM may contain duplicate data, the unencoded output is a better solution; CAM with unencoded outputs can distinguish multiple data locations.

CAM can be pre-loaded with data during configuration, or it can be written during system operation. In most cases, two clock cycles are required to write each word into CAM. When "don't care" bits are used, a third clock cycle is required.

APEX 20KC devices include an enhanced IOE, which drives the FastRow interconnect. The FastRow interconnect connects a column I/O pin directly to the LAB local interconnect within two MegaLAB structures. This feature provides fast setup times for pins that drive high fan-outs with complex logic, such as PCI designs. For fast bidirectional I/O timing, LE registers using local routing can improve setup times and OE timing. The APEX 20KC IOE also includes direct support for open-drain operation, giving faster clock-to-output for open-drain signals. Some programmable delays in the APEX 20KC IOE offer multiple levels of delay to fine-tune setup and hold time requirements. The Quartus II Compiler sets these delays by default to minimize setup time while providing a zero hold time.

The Quartus II Compiler uses the programmable inversion option to invert signals from the row and column interconnect automatically where appropriate. Because the APEX 20KC IOE offers one output enable per pin, the Quartus II Compiler can emulate open-drain operation efficiently.

The APEX 20KC IOE includes programmable delays that can be activated to ensure zero hold times, minimum clock-to-output times, input IOE register-to-core register transfers, or core-to-output IOE register transfers. A path in which a pin directly drives a register may require the delay to ensure zero hold time, whereas a path in which a pin drives a register through combinatorial logic may not require the delay.

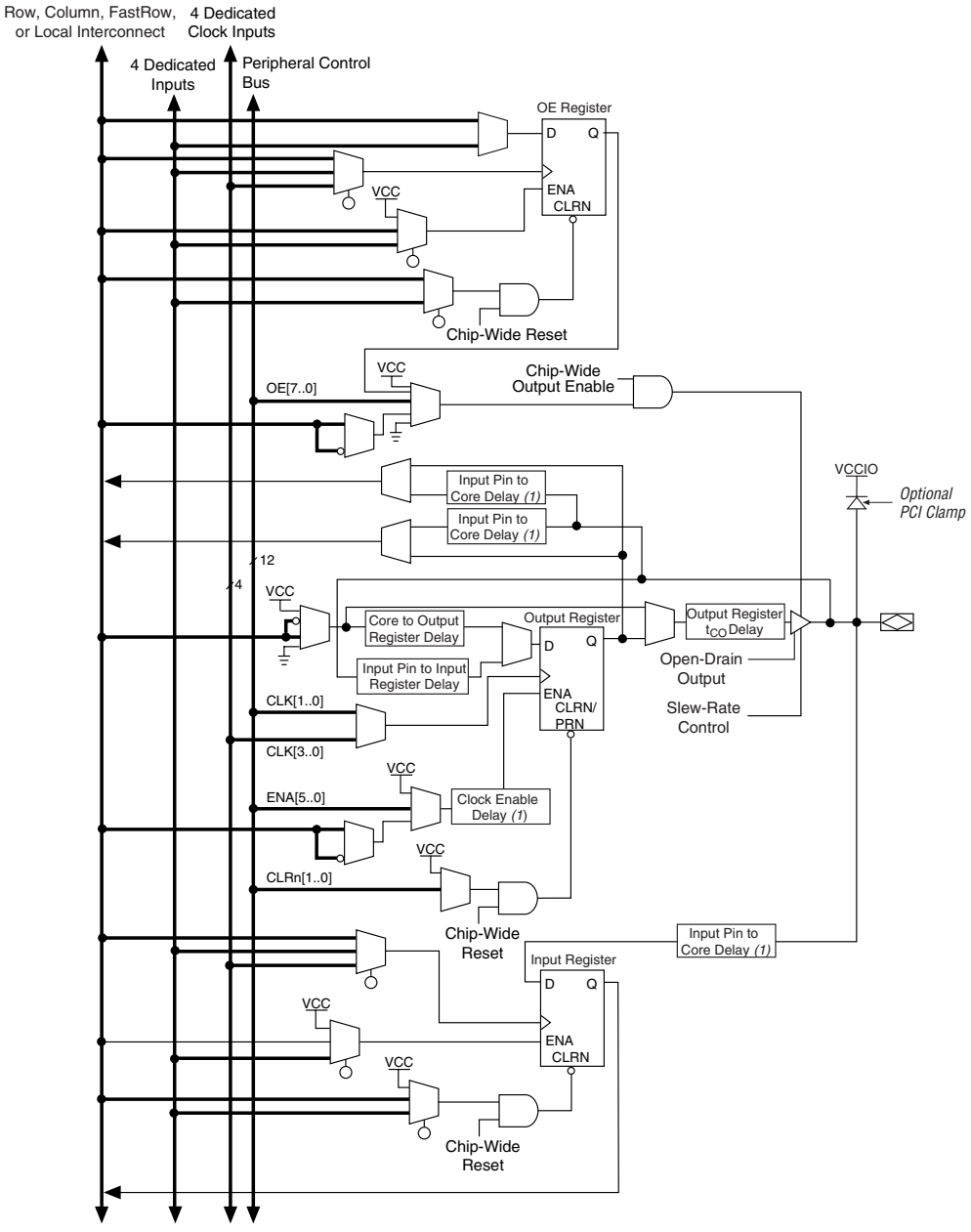
Table 9 describes the APEX 20KC programmable delays and their logic options in the Quartus II software.

Table 9. APEX 20KC Programmable Delay Chains

Programmable Delay	Quartus II Logic Option
Input pin to core delay	Decrease input delay to internal cells
Input pin to input register delay	Decrease input delay to input registers
Core to output register delay	Decrease input delay to output register
Output register t_{CO} delay	Increase delay to output pin
Clock enable delay	Increase clock enable delay

The Quartus II Compiler can program these delays automatically to minimize setup time while providing a zero hold time.

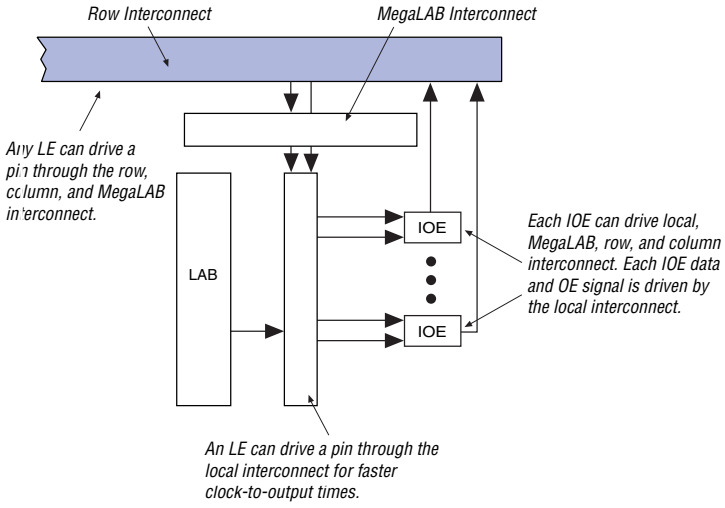
Figure 25. APEX 20KC Bidirectional I/O Registers *Notes (1), (2)*



Notes to Figure 25:
(1) This programmable delay has four settings: off and three levels of delay.
(2) The output enable and input registers are LE registers in the LAB adjacent to the bidirectional pin.

Each IOE drives a row, column, MegaLAB, or local interconnect when used as an input or bidirectional pin. A row IOE can drive a local, MegaLAB, row, and column interconnect; a column IOE can drive the column interconnect. Figure 26 shows how a row IOE connects to the interconnect.

Figure 26. Row IOE Connection to the Interconnect



Open-drain output pins on APEX 20KC devices (with a series resistor and a pull-up resistor to the 5.0-V supply) can drive 5.0-V CMOS input pins that require a V_{IH} of 3.5 V. When the pin is inactive, the trace will be pulled up to 5.0 V by the resistor. The open-drain pin will only drive low or tri-state; it will never drive high. The rise time is dependent on the value of the pull-up resistor and load impedance. The I_{OL} current specification should be considered when selecting a pull-up resistor.

ClockLock & ClockBoost Features

APEX 20KC devices support the ClockLock and ClockBoost clock management features, which are implemented with PLLs. The ClockLock circuitry uses a synchronizing PLL that reduces the clock delay and skew within a device. This reduction minimizes clock-to-output and setup times while maintaining zero hold times. The ClockBoost circuitry, which provides a clock multiplier, allows the designer to enhance device area efficiency by sharing resources within the device. The ClockBoost circuitry allows the designer to distribute a low-speed clock and multiply that clock on-device. APEX 20KC devices include a high-speed clock tree; unlike ASICs, the user does not have to design and optimize the clock tree. The ClockLock and ClockBoost features work in conjunction with the APEX 20KC device's high-speed clock to provide significant improvements in system performance and bandwidth. APEX 20KC devices in -7 and -8 speed grades have PLLs and support the ClockLock and ClockBoost features.

The ClockLock and ClockBoost features in APEX 20KC devices are enabled through the Quartus II software. External devices are not required to use these features.

APEX 20KC ClockLock Feature

APEX 20KC devices include up to four PLLs, which can be used independently. Two PLLs are designed for either general-purpose use or LVDS use (on devices that support LVDS I/O pins). The remaining two PLLs are designed for general-purpose use. The EP20K200C devices have two PLLs; the EP20K400C and larger devices have four PLLs.

The following sections describe some of the features offered by the APEX 20KC PLLs.

External PLL Feedback

The ClockLock circuit's output can be driven off-chip to clock other devices in the system; further, the feedback loop of the PLL can be routed off-chip. This feature allows the designer to exercise fine control over the I/O interface between the APEX 20KC device and another high-speed device, such as SDRAM.

Table 32. SSTL-3 Class II Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.0	3.3	3.6	V
V_{TT}	Termination voltage		V_{REF} – 0.05	V_{REF}	V_{REF} + 0.05	V
V_{REF}	Reference voltage		1.3	1.5	1.7	V
V_{IH}	High-level input voltage		V_{REF} + 0.2		V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage		–0.3		V_{REF} – 0.2	V
V_{OH}	High-level output voltage	I_{OH} = –16 mA *(1)*	V_{TT} + 0.8			V
V_{OL}	Low-level output voltage	I_{OL} = 16 mA *(2)*			V_{TT} – 0.8	V

Table 33. HSTL Class I I/O Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		1.71	1.8	1.89	V
V_{TT}	Termination voltage		V_{REF} – 0.05	V_{REF}	V_{REF} + 0.05	V
V_{REF}	Reference voltage		0.68	0.75	0.90	V
V_{IH}	High-level input voltage		V_{REF} + 0.1		V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage		–0.3		V_{REF} – 0.1	V
V_{OH}	High-level output voltage	I_{OH} = –8 mA *(1)*	V_{CCIO} – 0.4			V
V_{OL}	Low-level output voltage	I_{OL} = 8 mA *(2)*			0.4	V

Table 34. 3.3-V AGP I/O Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.15	3.3	3.45	V
V_{REF}	Reference voltage		0.39 × V_{CCIO}		0.41 × V_{CCIO}	V
V_{IH}	High-level input voltage		0.5 × V_{CCIO}		V_{CCIO} + 0.5	V
V_{IL}	Low-level input voltage				0.3 × V_{CCIO}	V
V_{OH}	High-level output voltage	I_{OUT} = –500 µA	0.9 × V_{CCIO}		3.6	V
V_{OL}	Low-level output voltage	I_{OUT} = 1,500 µA			0.1 × V_{CCIO}	V
I_I	Input pin leakage current	0 < V_{IN} < V_{CCIO}	–10		10	µA

Table 35. CTT I/O Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.0	3.3	3.6	V
V_{TT}/V_{REF} *(3)*	Termination and reference voltage		1.35	1.5	1.65	V
V_{IH}	High-level input voltage		V_{REF} + 0.2			V
V_{IL}	Low-level input voltage				V_{REF} – 0.2	V
I_I	Input pin leakage current	0 < V_{IN} < V_{CCIO}	–10		10	µA
V_{OH}	High-level output voltage	I_{OH} = –8 mA *(1)*	V_{REF} + 0.4			V
V_{OL}	Low-level output voltage	I_{OL} = 8 mA *(2)*			V_{REF} – 0.4	V
I_O	Output leakage current (when output is high Z)	GND ≤ V_{OUT} ≤ V_{CCIO}	–10		10	µA

Notes to Tables 21 through 35:

(1) The I_{OH} parameter refers to high-level output current.
(2) The I_{OL} parameter refers to low-level output current. This parameter applies to open-drain pins as well as output pins.
(3) V_{REF} specifies center point of switching range.

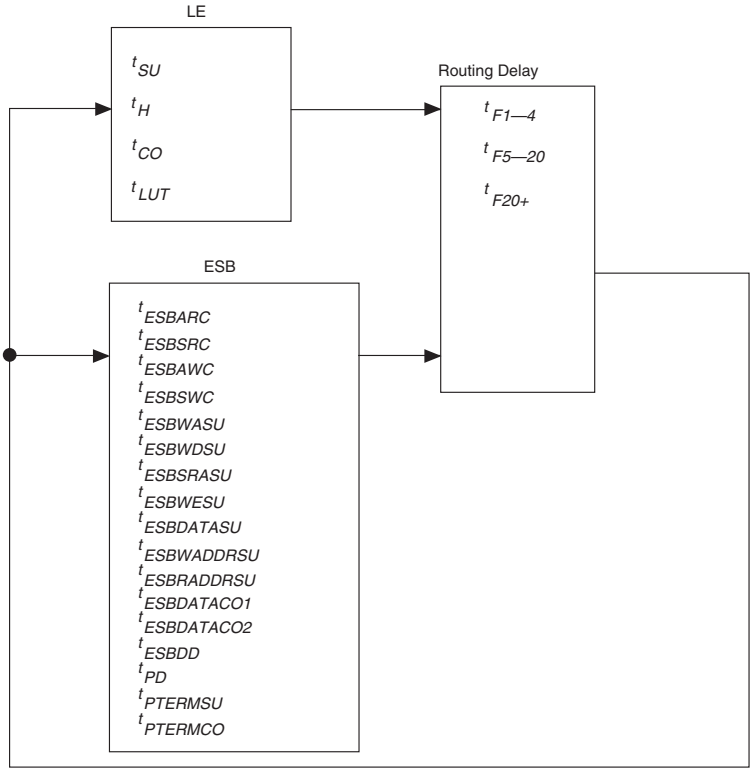
Figure 31 shows the output drive characteristics of APEX 20KC devices.

Timing Model

The high-performance FastTrack and MegaLAB interconnect routing resources ensure predictable performance, accurate simulation, and accurate timing analysis. This predictable performance contrasts with that of FPGAs, which use a segmented connection scheme and therefore have unpredictable performance.

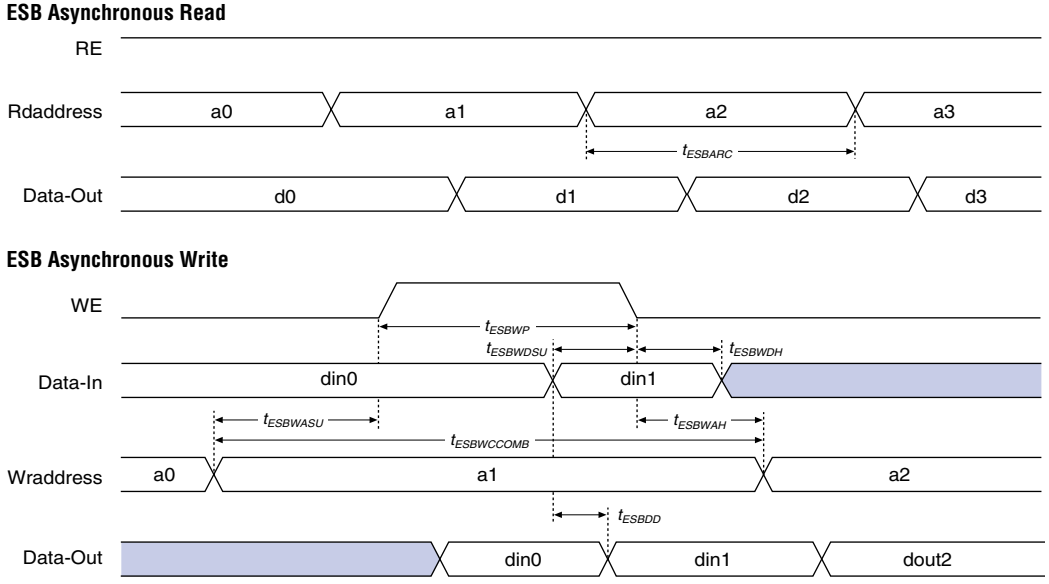
Figure 32 shows the f_{MAX} timing model for APEX 20KC devices.

Figure 32. f_{MAX} Timing Model



Figures 33 and 34 show the asynchronous and synchronous timingwaveforms, respectively, for the ESB macroparameters in Table 37.

Figure 33. ESB Asynchronous Timing Waveforms



Tables 44 through 67 show the f_{MAX} and external timing parameters for EPC20K200C, EP20K400C, EP20K600C, and EP20K1000C devices.

Table 44. EP20K200C f_{MAX} LE Timing Microparameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.01		0.01		0.01		ns
t_{H}	0.10		0.10		0.10		ns
t_{CO}		0.27		0.30		0.32	ns
t_{LUT}		0.65		0.78		0.92	ns

Table 45. EP20K200C f_{MAX} ESB Timing Microparameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.30		1.51		1.69	ns
t_{ESBSRC}		2.35		2.49		2.72	ns
t_{ESBAWC}		2.92		3.46		3.86	ns
t_{ESBSWC}		3.05		3.44		3.85	ns
$t_{ESBWASU}$	0.45		0.50		0.54		ns
t_{ESBWAH}	0.44		0.50		0.55		ns
$t_{ESBWDSU}$	0.57		0.63		0.68		ns
t_{ESBWDH}	0.44		0.50		0.55		ns
$t_{ESBRASU}$	1.25		1.43		1.56		ns
t_{ESBRAH}	0.00		0.03		0.11		ns
$t_{ESBWESU}$	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	2.01		2.27		2.45		ns
$t_{ESBWADDRSU}$	–0.20		–0.24		–0.28		ns
$t_{ESBRADDRSU}$	0.02		0.00		–0.02		ns
$t_{ESBDATACO1}$		1.09		1.28		1.43	ns
$t_{ESBDATACO2}$		2.10		2.52		2.82	ns
t_{ESBDD}		2.50		2.97		3.32	ns
t_{PD}		1.48		1.78		2.00	ns
$t_{PTERMSU}$	0.58		0.72		0.81		ns
$t_{PTERMCO}$		1.10		1.29		1.45	ns

Table 57. EP20K600C f_{MAX} ESB Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.30		1.51		1.69	ns
t_{ESBSRC}		2.35		2.49		2.72	ns
t_{ESBAWC}		2.92		3.46		3.86	ns
t_{ESBSWC}		3.05		3.44		3.85	ns
$t_{ESBWASU}$	0.45		0.50		0.54		ns
t_{ESBWAH}	0.44		0.50		0.55		ns
$t_{ESBWDSU}$	0.57		0.63		0.68		ns
t_{ESBWDH}	0.44		0.50		0.55		ns
$t_{ESBRASU}$	1.25		1.43		1.56		ns
t_{ESBRAH}	0.00		0.03		0.11		ns
$t_{ESBWESU}$	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	2.01		2.27		2.45		ns
$t_{ESBWADDRSU}$	–0.20		–0.24		–0.28		ns
$t_{ESBRADDRSU}$	0.02		0.00		–0.02		ns
$t_{ESBDATACO1}$		1.09		1.28		1.43	ns
$t_{ESBDATACO2}$		2.10		2.52		2.82	ns
t_{ESBDD}		2.50		2.97		3.32	ns
t_{PD}		1.48		1.78		2.00	ns
$t_{PTERMSU}$	0.58		0.72		0.81		ns
$t_{PTERMCO}$		1.10		1.29		1.45	ns

Table 58. EP20K600C f_{MAX} Routing Delays

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.15		0.16		0.18	ns
t_{F5-20}		0.94		1.05		1.20	ns
t_{F20+}		1.76		1.98		2.23	ns

Table 59. EP20K600C Minimum Pulse Width Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	1.33		1.66		2.00		ns
t_{CL}	1.33		1.66		2.00		ns
t_{CLRP}	0.20		0.20		0.20		ns
t_{PREP}	0.20		0.20		0.20		ns
t_{ESBCH}	1.33		1.66		2.00		ns
t_{ESBCL}	1.33		1.66		2.00		ns
t_{ESBWP}	1.05		1.28		1.44		ns
t_{ESBRP}	0.87		1.06		1.19		ns

Table 60. EP20K600C External Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	1.28		1.40		1.45		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	4.29	2.00	4.77	2.00	5.11	ns
$t_{INSUPLL}$	0.80		0.91		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	2.37	0.50	2.63	-	-	ns

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